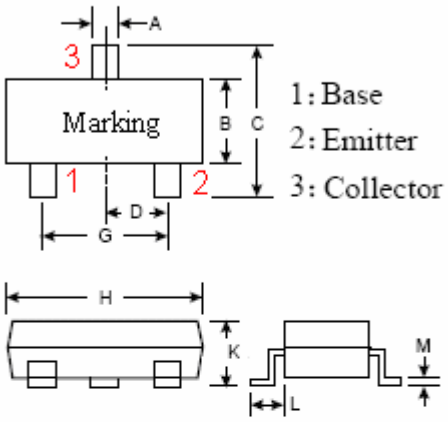
isc Silicon NPN RF Transistor 2SC4262

SOT-323 package



DIM	mm	
	MIN	MAX
A	0.30	0.40
B	1.15	1.35
C	2.00	2.40
D	0.65	
H	1.80	2.20
K	0.80	1.00
M	0.10	0.25

DESCRIPTION

- Low Noise
- High Gain

APPLICATIONS

- Designed for use in UHF~ VHF local oscillator.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	20	V
V_{CEO}	Collector-Emitter Voltage	15	V
V_{EBO}	Emitter-Base Voltage	3.0	V
I_C	Collector Current-Continuous	50	mA
P_C	Collector Power Dissipation @T_C=25℃	0.1	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C= 10μA ; I_E= 0	20			V
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= 1mA ; R_{BE}= ∞	15			V
I_{CBO}	Collector Cutoff Current	V_{CB}= 15V; I_E= 0			0.5	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 3V; I_C= 0			1.0	μA
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 20mA ; I_B= 4mA			0.5	V
h_{FE}	DC Current Gain	I_C= 5mA ; V_{CE}= 10V	50		200	
f_T	Current-Gain—Bandwidth Product	I_C= 5mA ; V_{CE}= 10V	1.4	2.9		GHz
C_{OB}	Output Capacitance	I_E= 0 ; V_{CB}= 10V;f= 1.0MHz			1.0	pF

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